

## PowerMOS transistor

PHX1N40

## GENERAL DESCRIPTION

N-channel enhancement mode field-effect power transistor in a full pack plastic envelope featuring high avalanche energy capability, stable off-state characteristics, fast switching and high thermal cycling performance with low thermal resistance. Intended for use in Switched Mode Power Supplies (SMPS), motor control circuits and general purpose switching applications.

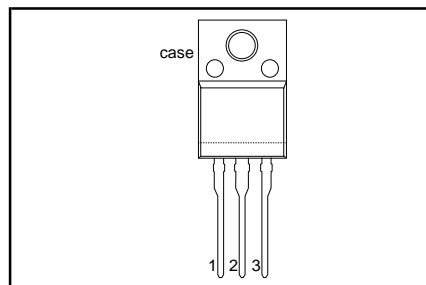
## QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{DS}$	Drain-source voltage	400	V
$I_D$	Drain current (DC)	1.7	A
$P_{tot}$	Total power dissipation	25	W
$R_{DS(ON)}$	Drain-source on-state resistance	3.5	$\Omega$

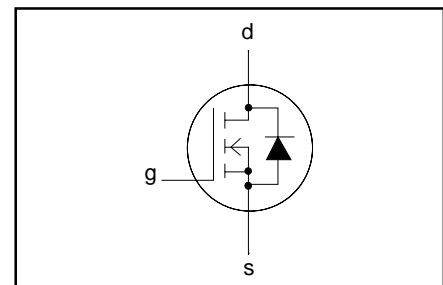
## PINNING - SOT186A

PIN	DESCRIPTION
1	gate
2	drain
3	source
case	isolated

## PIN CONFIGURATION



## SYMBOL



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_D$	Continuous drain current	$T_{hs} = 25\text{ }^\circ\text{C}; V_{GS} = 10\text{ V}$	-	1.7	A
$I_{DM}$	Pulsed drain current	$T_{hs} = 100\text{ }^\circ\text{C}; V_{GS} = 10\text{ V}$	-	1.1	A
$P_D$	Total dissipation	$T_{hs} = 25\text{ }^\circ\text{C}$	-	7	A
$\Delta P_D / \Delta T_{mb}$	Linear derating factor	$T_{hs} = 25\text{ }^\circ\text{C}$	-	25	W
$V_{GS}$	Gate-source voltage	$T_{hs} > 25\text{ }^\circ\text{C}$	-	0.2	W/K
$E_{AS}$	Single pulse avalanche energy	$V_{DD} \leq 50\text{ V};$ starting $T_j = 25\text{ }^\circ\text{C}; R_{GS} = 50\text{ }\Omega;$ $V_{GS} = 10\text{ V}$	-	$\pm 30$	V
$I_{AS}$	Peak avalanche current	$V_{DD} \leq 50\text{ V};$ starting $T_j = 25\text{ }^\circ\text{C}; R_{GS} = 50\text{ }\Omega;$ $V_{GS} = 10\text{ V}$	-	100	mJ
$T_j, T_{stg}$	Operating junction and storage temperature range		-55	150	$^\circ\text{C}$

## ISOLATION LIMITING VALUE &amp; CHARACTERISTIC

$T_{hs} = 25\text{ }^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{isol}$	R.M.S. isolation voltage from all three terminals to external heatsink	$f = 50\text{-}60\text{ Hz};$ sinusoidal waveform; $R.H. \leq 65\%;$ clean and dustfree	-		2500	V
$C_{isol}$	Capacitance from T2 to external heatsink	$f = 1\text{ MHz}$	-	10	-	pF

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## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-hs}$	Thermal resistance junction to heatsink	with heatsink compound	-	-	5	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient		-	55	-	K/W

## ELECTRICAL CHARACTERISTICS

 $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 0.25\text{ mA}$	400	-	-	V
$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	Drain-source breakdown voltage temperature coefficient	$V_{DS} = V_{GS}; I_D = 0.25\text{ mA}$	-	0.45	-	V/K
$R_{DS(ON)}$	Drain-source on resistance	$V_{GS} = 10\text{ V}; I_D = 1.25\text{ A}$	-	2.0	3.5	$\Omega$
$V_{GS(TO)}$	Gate threshold voltage	$V_{DS} = V_{GS}; I_D = 0.25\text{ mA}$	2.0	3.0	4.0	V
$g_{fs}$	Forward transconductance	$V_{DS} = 30\text{ V}; I_D = 1.25\text{ A}$	0.5	1.5	-	S
$I_{DSS}$	Drain-source leakage current	$V_{DS} = 400\text{ V}; V_{GS} = 0\text{ V}$	-	1	25	$\mu\text{A}$
$I_{GSS}$	Gate-source leakage current	$V_{DS} = 320\text{ V}; V_{GS} = 0\text{ V}; T_j = 125\text{ }^\circ\text{C}$ $V_{GS} = \pm 30\text{ V}; V_{DS} = 0\text{ V}$	-	30	250	$\mu\text{A}$
$Q_{g(tot)}$	Total gate charge	$I_D = 2.5\text{ A}; V_{DD} = 320\text{ V}; V_{GS} = 10\text{ V}$	-	20	25	nC
$Q_{gs}$	Gate-source charge		-	2	3	nC
$Q_{gd}$	Gate-drain (Miller) charge		-	8	12	nC
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 200\text{ V}; I_D = 2.5\text{ A};$ $R_G = 24\text{ }\Omega; R_D = 78\text{ }\Omega$	-	10	-	ns
$t_r$	Turn-on rise time		-	25	-	ns
$t_{d(off)}$	Turn-off delay time		-	46	-	ns
$t_f$	Turn-off fall time		-	25	-	ns
$L_d$	Internal drain inductance	Measured from drain lead 6 mm from package to centre of die	-	4.5	-	nH
$L_s$	Internal source inductance	Measured from source lead 6 mm from package to source bond pad	-	7.5	-	nH
$C_{iss}$	Input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$	-	240	-	pF
$C_{oss}$	Output capacitance		-	44	-	pF
$C_{rss}$	Feedback capacitance		-	26	-	pF

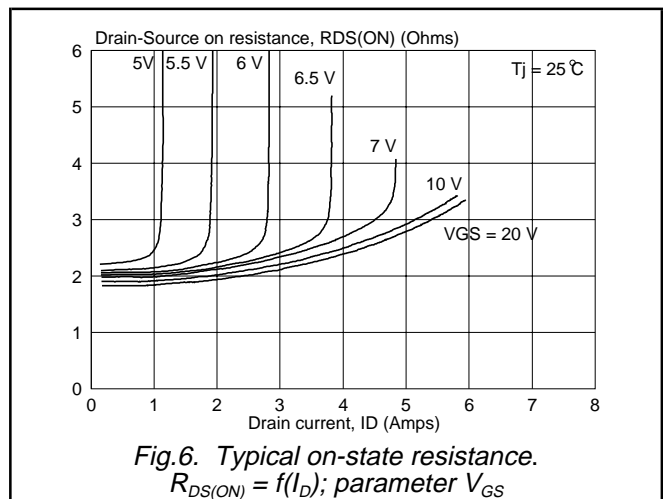
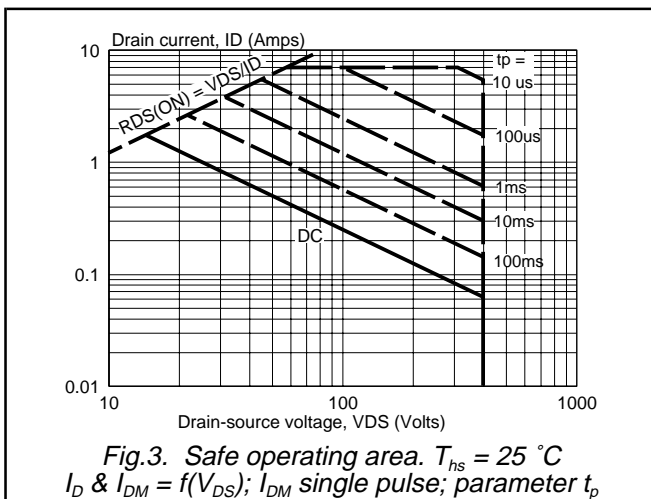
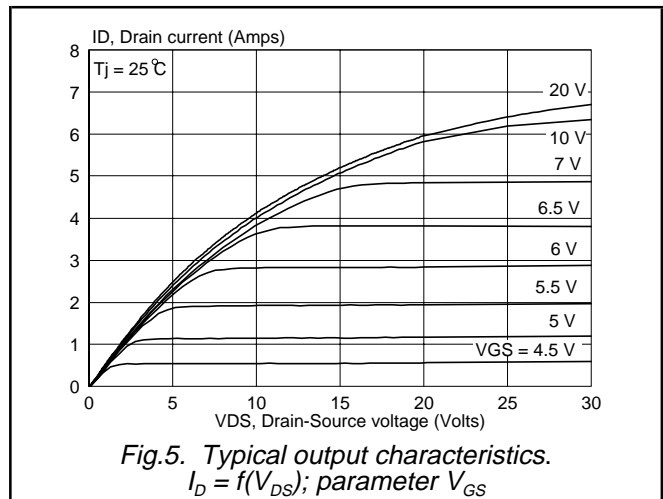
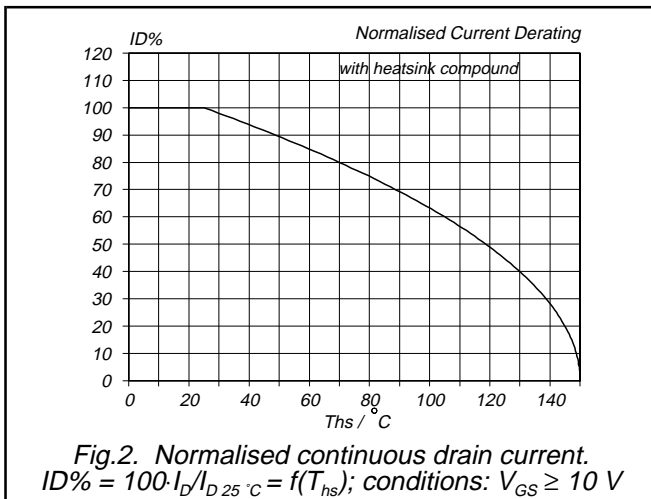
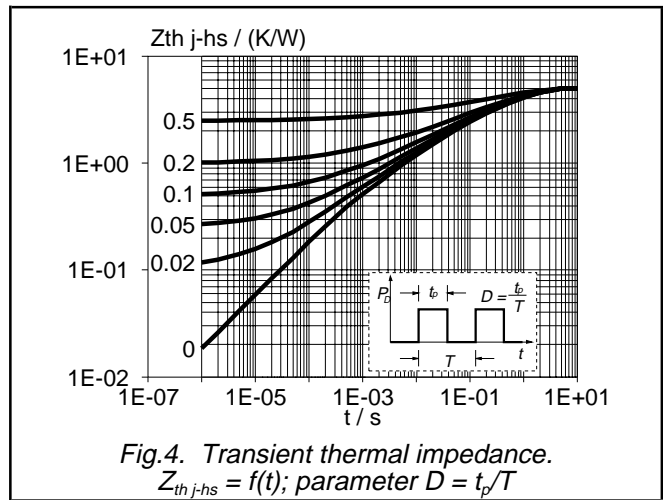
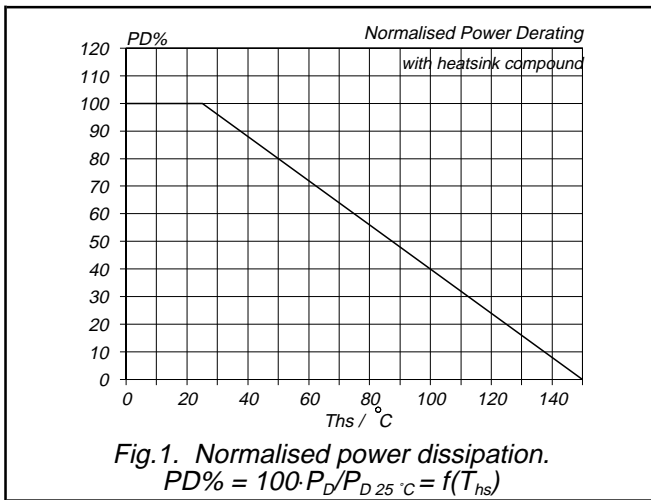
## SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

 $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_S$	Continuous source current (body diode)	$T_{hs} = 25\text{ }^\circ\text{C}$	-	-	2.5	A
$I_{SM}$	Pulsed source current (body diode)	$T_{hs} = 25\text{ }^\circ\text{C}$	-	-	10	A
$V_{SD}$	Diode forward voltage	$I_S = 2.5\text{ A}; V_{GS} = 0\text{ V}$	-	-	1.2	V
$t_{rr}$	Reverse recovery time	$I_S = 2.5\text{ A}; V_{GS} = 0\text{ V};$ $di/dt = 100\text{ A}/\mu\text{s}$	-	200	-	ns
$Q_{rr}$	Reverse recovery charge		-	2.0	-	$\mu\text{C}$

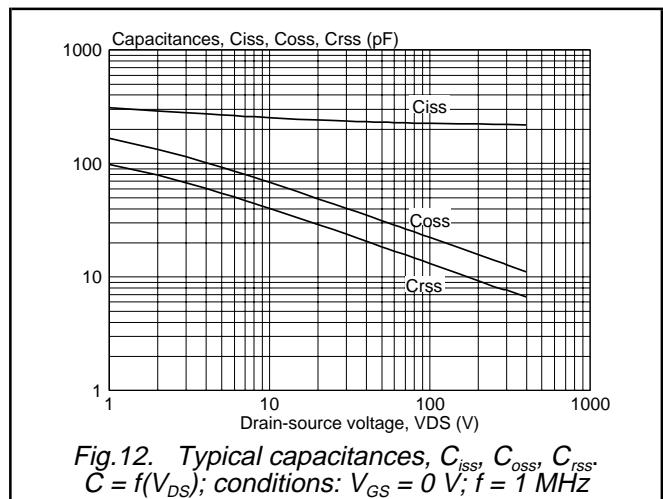
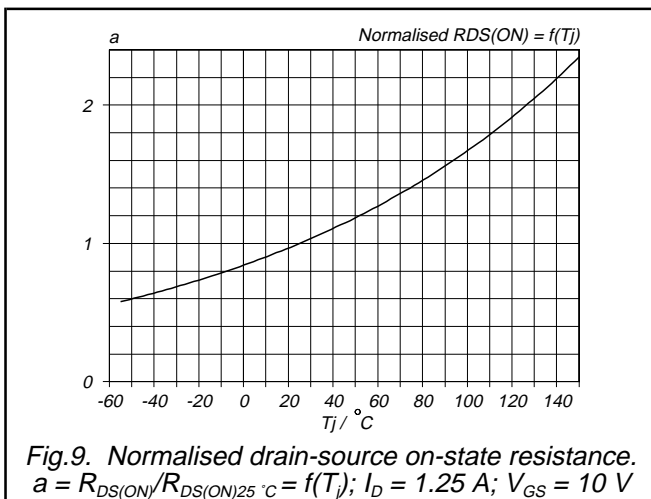
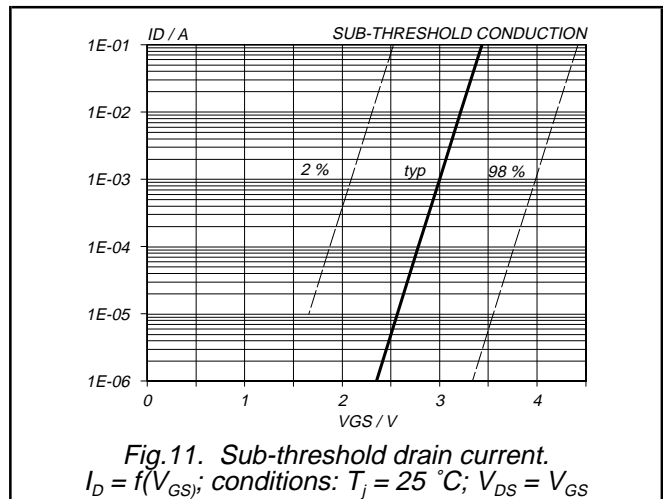
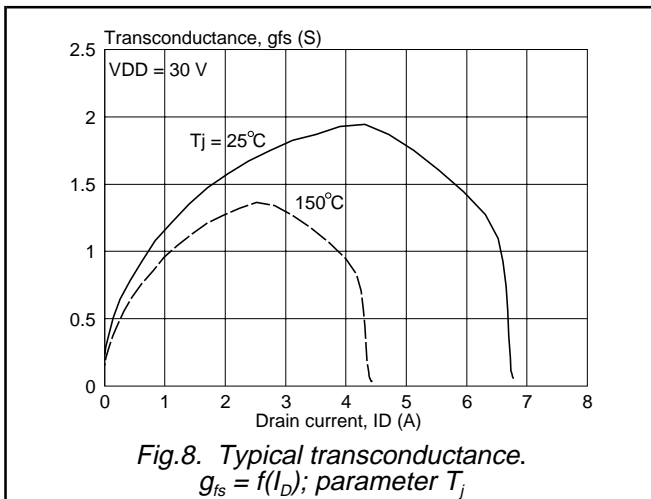
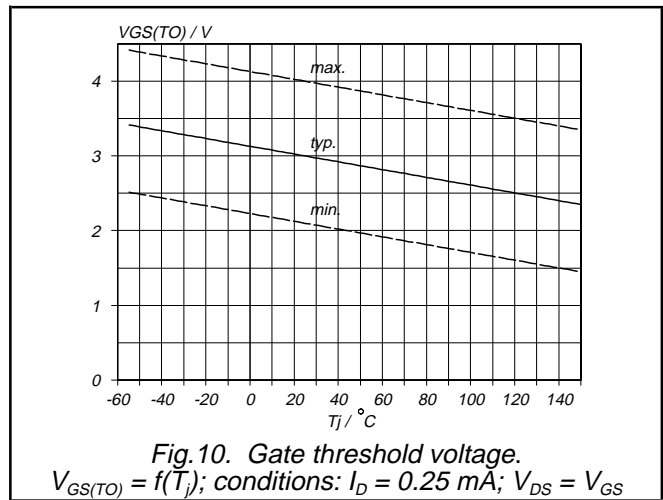
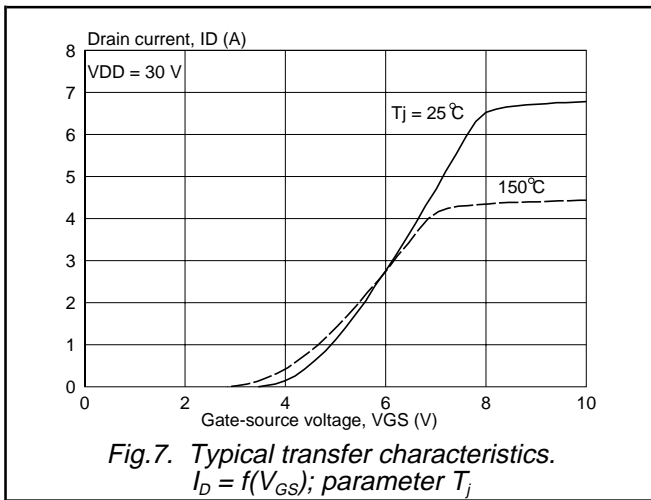
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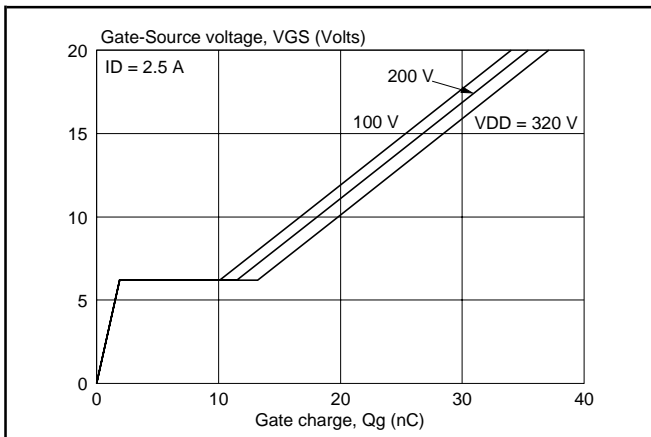


Fig.13. Typical turn-on gate-charge characteristics.  
 $V_{GS} = f(Q_G)$ ; parameter  $V_{DS}$

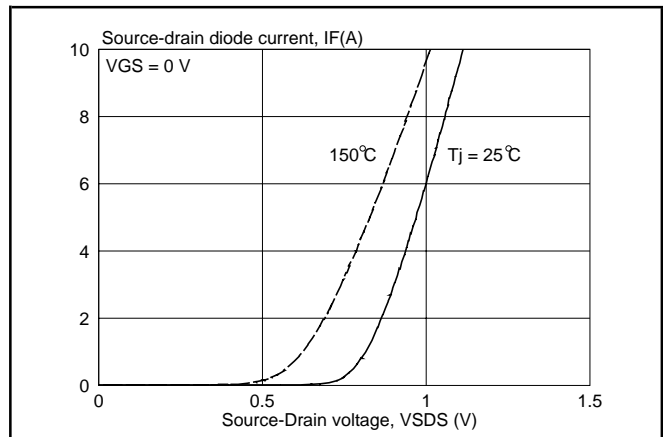


Fig.16. Source-Drain diode characteristic.  
 $I_F = f(V_{SDS})$ ; parameter  $T_j$

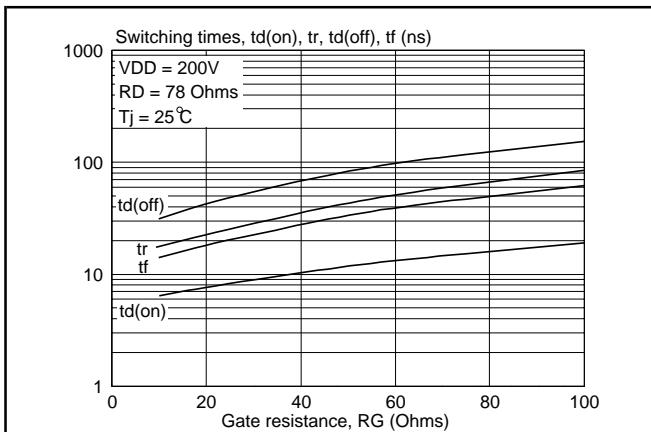


Fig.14. Typical switching times.  
 $t_{d(on)}, t_r, t_{d(off)}, t_f = f(R_G)$

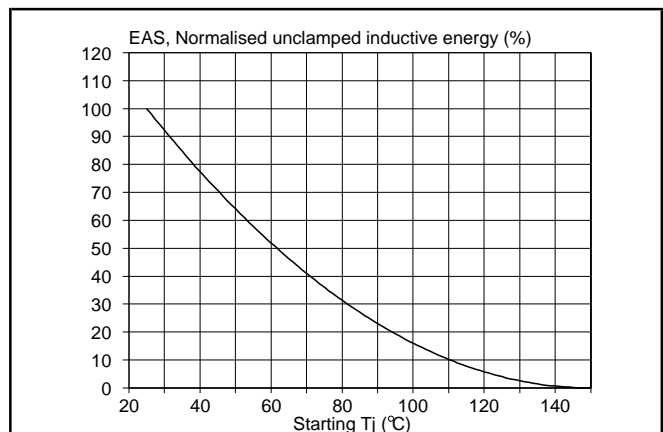


Fig.17. Normalised unclamped inductive energy.  
 $E_{AS} \% = f(T_j)$

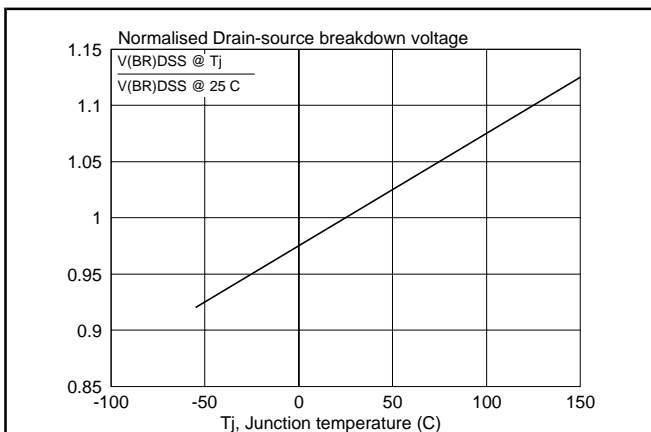


Fig.15. Normalised drain-source breakdown voltage.  
 $V_{(BR)DSS} / V_{(BR)DSS\ 25\ ^\circ C} = f(T_j)$

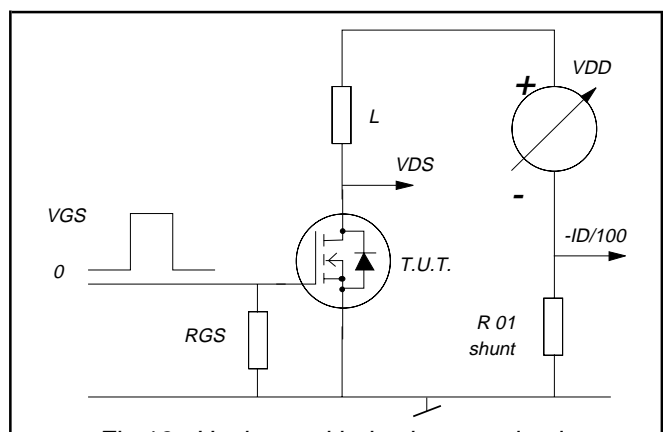


Fig.18. Unclamped inductive test circuit.  
 $E_{AS} = 0.5 \cdot L I_D^2 \cdot V_{(BR)DSS} / (V_{(BR)DSS} - V_{DD})$

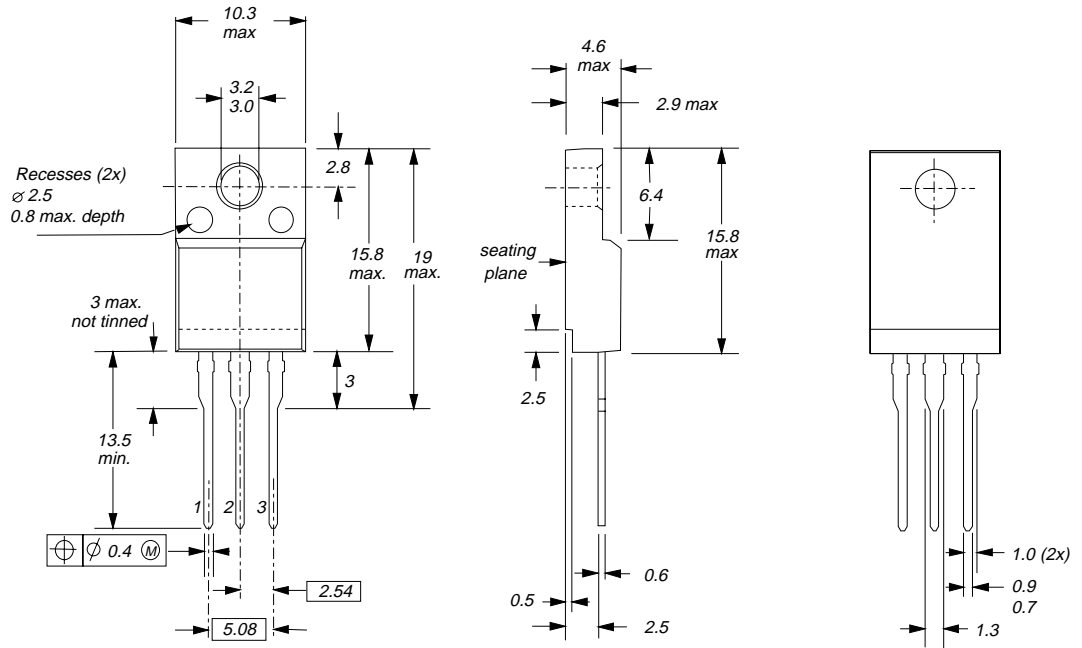
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**MECHANICAL DATA**

*Dimensions in mm*

*Net Mass: 2 g*



*Fig. 19. SOT186A; The seating plane is electrically isolated from all terminals.*

**Notes**

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Refer to mounting instructions for F-pack envelopes.
3. Epoxy meets UL94 V0 at 1/8".

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**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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